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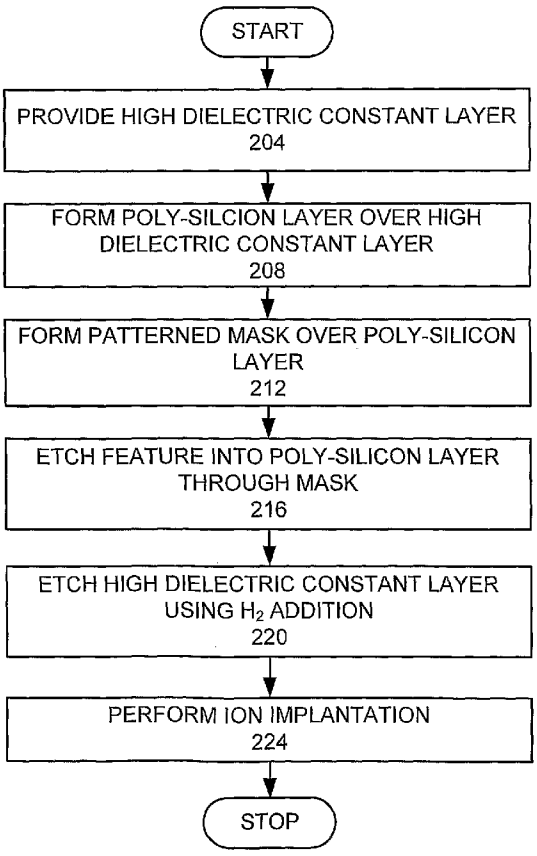
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[Continued on next page]

(54) Title: SELECTIVITY ETCH OF FILMS WITH HIGH DIELECTRIC CONSTANT WITH H_2 ADDITION



(57) Abstract: A method for selectively etching a high k layer with respect to a silicon based material is provided. The high k layer is placed into an etch chamber. An etchant gas is provided into the etch chamber, wherein the etchant gas comprises H_2. A plasma is generated from the etchant gas to selectively etch the high k layer with respect to a silicon based material.

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